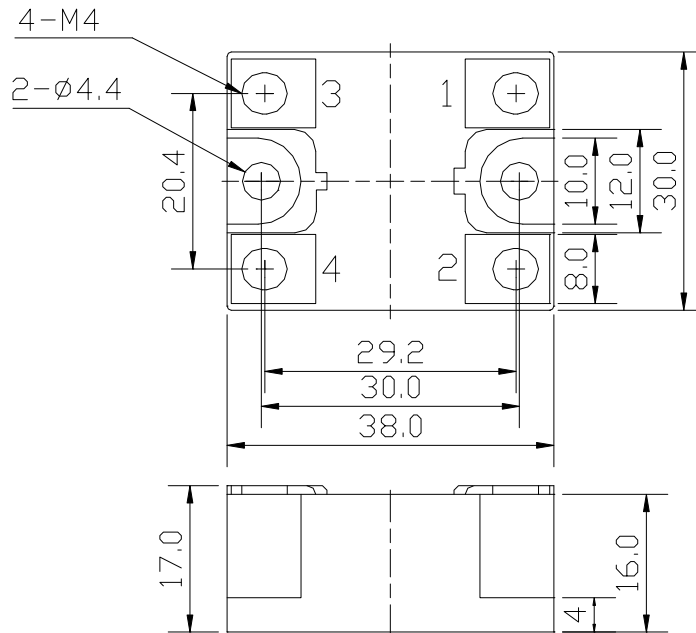
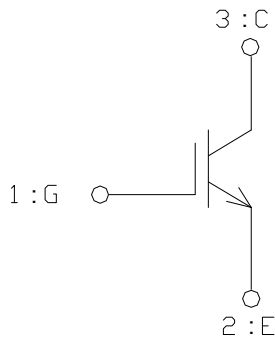


□ 回路図 : **CIRCUIT**

□ 外形寸法図 : **OUTLINE DRAWING**

Dimension : [mm]



□ 最大定格 : **MAXIMUM RATINGS** (T_c=25° C)

Item	Symbol	Rated Value	Unit
コレクタ・エミッタ間電圧 Collector-Emitter Voltage	V _{CEs}	600	V
ゲート・エミッタ間電圧 Gate-Emitter Voltage	V _{GES}	±20	V
コレクタ電流 Collector Current	DC	50	A
	1ms	100	
コレクタ損失 Collector Power Dissipation	P _c	250	W
接合温度 Junction Temperature Range	T _j	-40~+150	°C
保存温度 Storage Temperature Range	T _{stg}	-40~+125	°C
絶縁耐圧 (Terminal to Base AC, 1minute) Isolation Voltage	V _{iso}	2,500	V(RMS)
締め付けトルク Mounting Torque	Module Base to Heatsink	1.4 (14.3)	N·m (kgf·cm)
	Busbar to Main Terminal		

□ 電気的特性 : **ELECTRICAL CHARACTERISTICS** (T_c=25° C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
コレクタ遮断電流 Collector-Emitter Cut-Off Current	I _{CEs}	V _{CE} = 600V, V _{GE} = 0V	-	-	1.0	mA
ゲート漏れ電流 Gate-Emitter Leakage Current	I _{GES}	V _{GE} = ±20V, V _{CE} = 0V	-	-	1.0	μA
コレクタ・エミッタ間飽和電圧 Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 50A, V _{GE} = 15V	-	2.1	2.6	V
ゲートしきい値電圧 Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{CE} = 5V, I _C = 50mA	4.0	-	8.0	V
入力容量 Input Capacitance	C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f= 1MHz	-	2,500	-	pF
スイッチング時間 Switching Time	上昇時間 Rise Time	V _{CC} = 300V R _L = 6.0Ω R _G = 20Ω V _{GE} = ±15V	-	0.15	0.30	μs
	ターンオン時間 Turn-on Time		-	0.25	0.40	
	下降時間 Fall Time		-	0.10	0.35	
	ターンオフ時間 Turn-off Time		-	0.35	0.70	

□ 熱的特性 : **THERMAL CHARACTERISTICS**

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
熱抵抗 Thermal Impedance	R _{th(j-c)}	Junction to Case (T _c チップ直下での測定点)	-	-	0.50	°C/W

Fig.1- Output Characteristics (Typical)

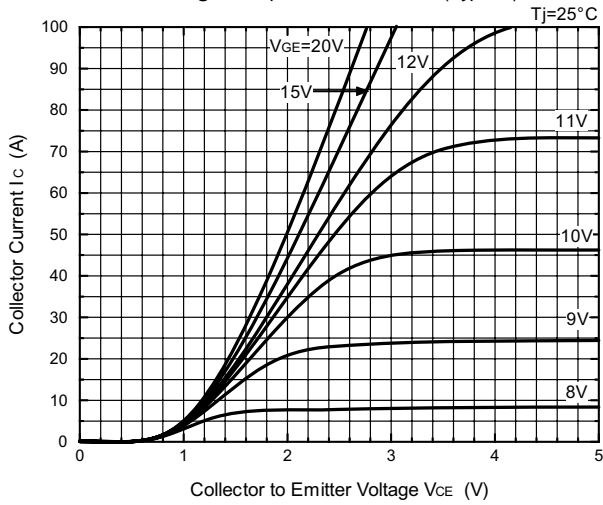


Fig.2- Output Characteristics (Typical)

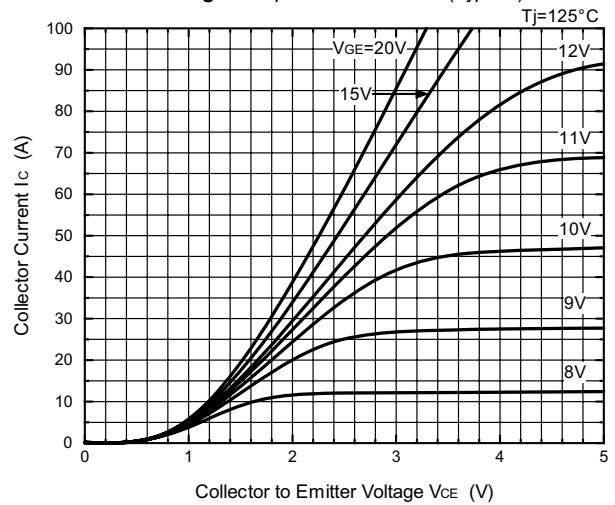


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

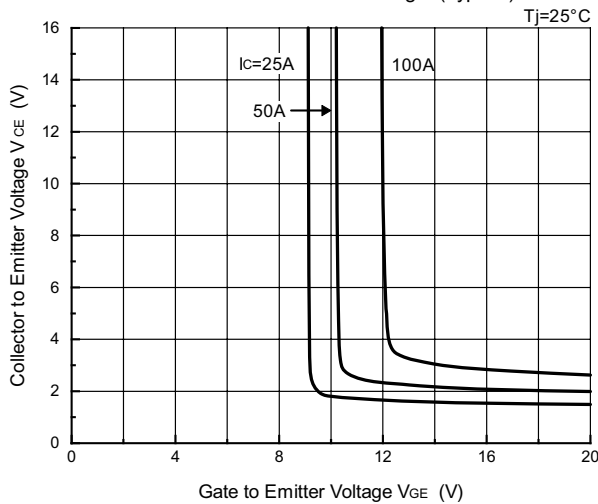


Fig.4- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

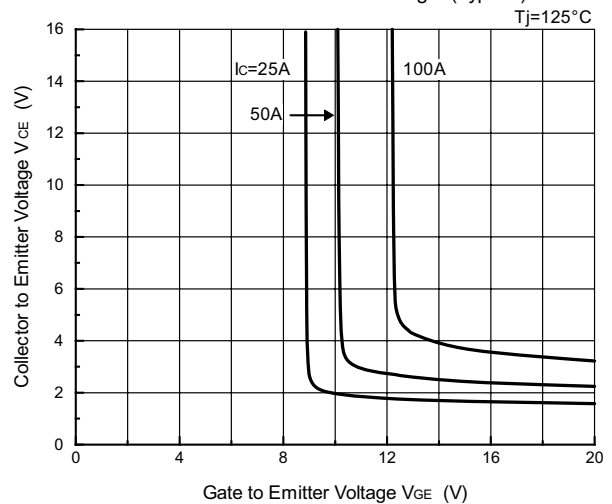


Fig.5- Gate Charge vs. Collector to Emitter Voltage (Typical)

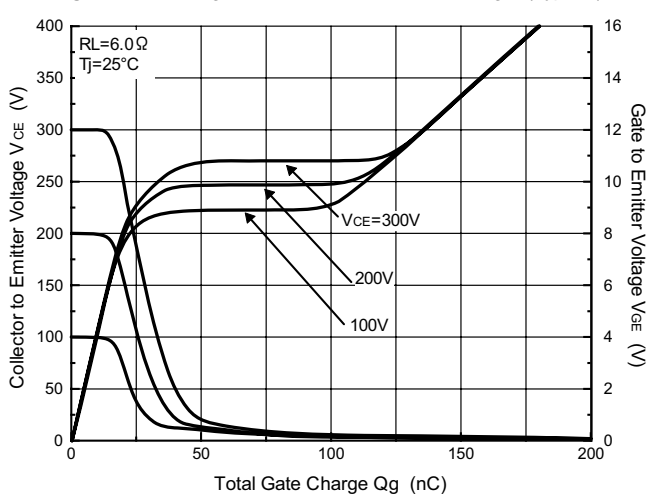


Fig.6- Capacitance vs. Collector to Emitter Voltage (Typical)

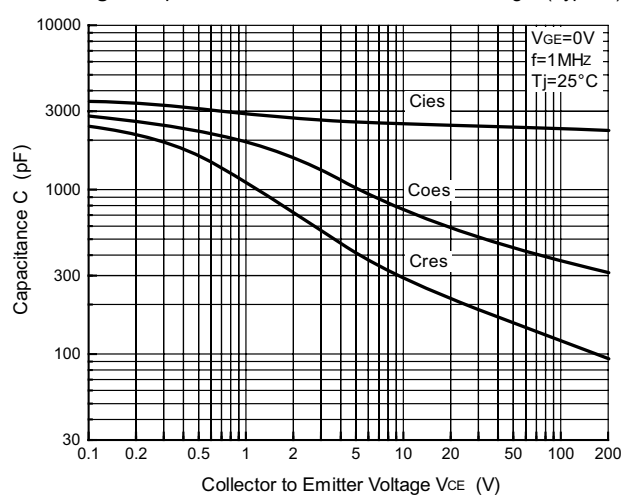


Fig.7- Collector Current vs. Switching Time (Typical)

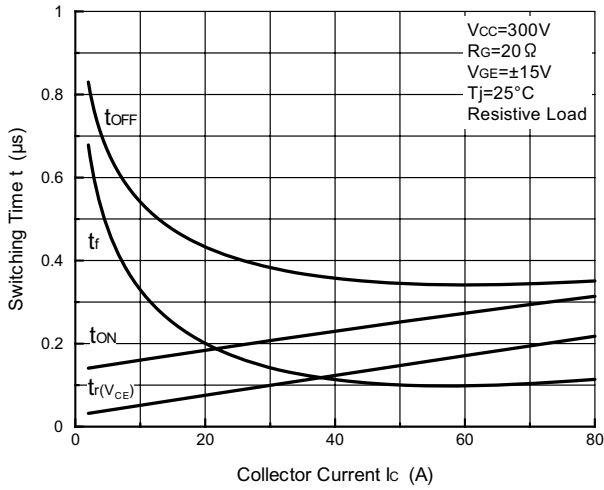


Fig.8- Series Gate Impedance vs. Switching Time (Typical)

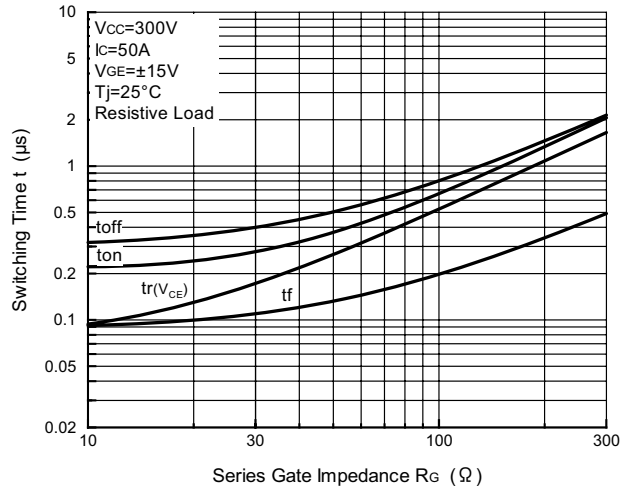


Fig.9- Collector Current vs. Switching Time

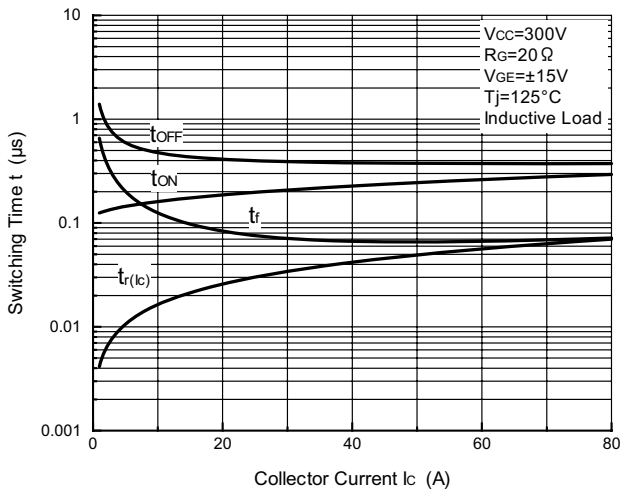


Fig.10- Series Gate Impedance vs. Switching Time

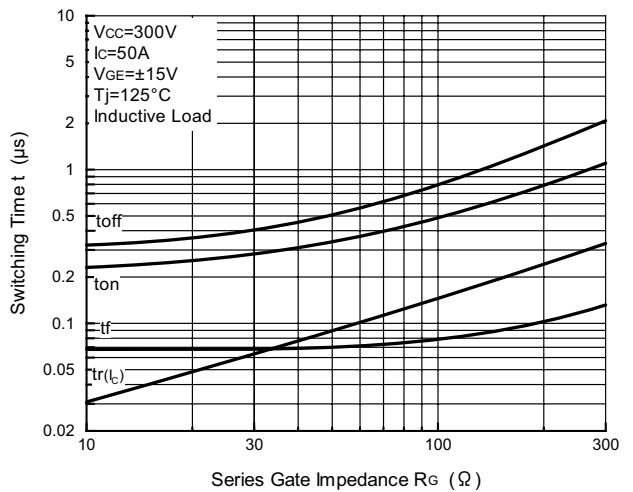


Fig.11- Collector Current vs. Switching Loss

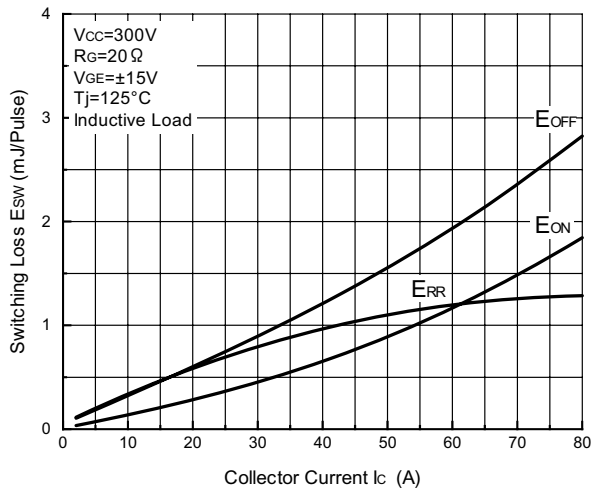


Fig.12- Series Gate Impedance vs. Switching Loss

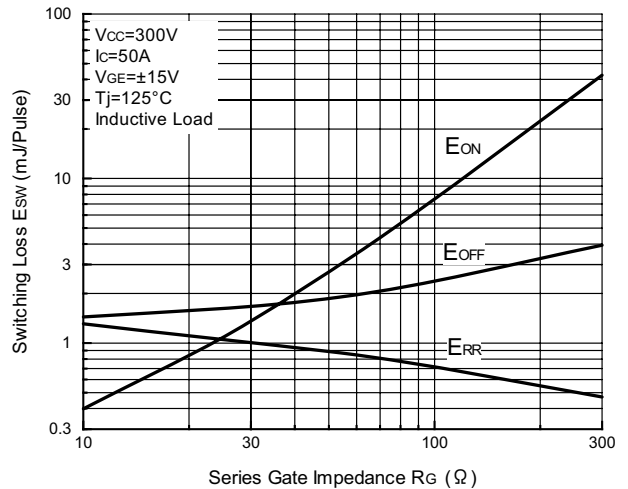


Fig.13- Reverse Bias Safe Operating Area

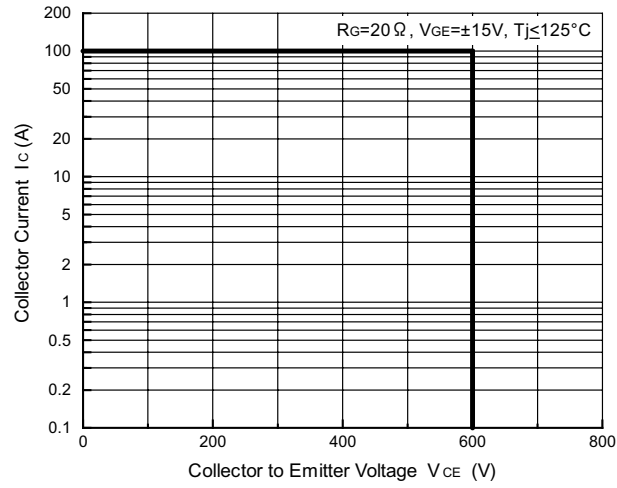


Fig.14- Transient Thermal Impedance

